



IXTA4N65X2 Information



For Reference Only

Part Number IXTA4N65X2

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 4A X2 TO-263

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXTA4N65X2 Specifications

Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature Jordan Gate Mose Mose Mount Surface Mount		
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs8.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds455pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)80W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface Mount		Transistors - FETs, MOSFETs - Single
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs8.3nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds455pF @ 25 VVgs (Max)±30 VFET Feature-Power Dissipation (Max)80 W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 2A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface Mount	Series	-
Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs8.3nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds455pF @ 25 VVgs (Max)±30 VFET Feature-Power Dissipation (Max)80 W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 2A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface Mount	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.3nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 455pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 80W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) $Vgs(th)$ (Max) @ Id SV @ $250\mu A$ SV @ $10V$ SV — $10V$ S	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 8.3nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 455pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Current - Continuous Drain (Id) @ 25°C	4A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 455pF @ 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type 8.3nC @ 10V 455pF @ 25V 430V FET Feature - Surface Mount	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 455pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 80W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)80W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface Mount	Gate Charge (Qg) (Max) @ Vgs	8.3nC @ 10V
FET Feature - Power Dissipation (Max) 80W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Input Capacitance (Ciss) (Max) @ Vds	455pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 850 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$ Mounting Type Surface Mount	Power Dissipation (Max)	80W (Tc)
Mounting Type Surface Mount	Rds On (Max) @ Id, Vgs	850 mOhm @ 2A, 10V
	Operating Temperature	-55°C ~ 150°C (TJ)
Supplier Device Package TO-263	Mounting Type	Surface Mount
2411-11-201-11-11-10-11-11-11-11-11-11-11-11-11-1	Supplier Device Package	TO-263
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Report errors?		Report errors?

IXTA4N65X2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTA4N65X2 Payment Methods



















IXTA4N65X2 Shipping Methods













If you have any question about IXTA4N65X2, please do not hesitate to contact us!

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